



PSMN8R0-30YLC

N-channel 30 V 7.9 mΩ logic level MOSFET in LPAK using NextPower technology

Rev. 2 — 1 September 2011

Product data sheet

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, QOSS for high system efficiencies at low and high loads

1.3 Applications

- DC-to-DC converters
- Synchronous buck regulator
- Load switching

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	-	30	V
I_D	drain current	$T_{mb} = 25\text{ °C}$; $V_{GS} = 10\text{ V}$; see Figure 1	-	-	54	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; see Figure 2	-	-	42	W
T_j	junction temperature		-55	-	175	°C
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}$; $I_D = 15\text{ A}$; $T_j = 25\text{ °C}$; see Figure 12	-	8.5	10	mΩ
		$V_{GS} = 10\text{ V}$; $I_D = 15\text{ A}$; $T_j = 25\text{ °C}$; see Figure 12	-	6.7	7.9	mΩ

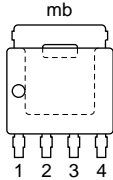
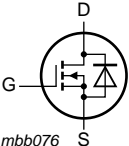


Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 4.5\text{ V}$; $I_D = 15\text{ A}$; $V_{DS} = 15\text{ V}$; see Figure 14 ; see Figure 15	-	2.3	-	nC
$Q_{G(tot)}$	total gate charge	$V_{GS} = 4.5\text{ V}$; $I_D = 15\text{ A}$; $V_{DS} = 15\text{ V}$; see Figure 14 ; see Figure 15	-	7	-	nC

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		
			SOT669 (LPAK; Power-SO8)	

3. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
PSMN8R0-30YLC	LPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	30	V
V_{DGR}	drain-gate voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$; $R_{GS} = 20\text{ k}\Omega$	-	30	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ °C}$; see Figure 1	-	54	A
		$V_{GS} = 10\text{ V}$; $T_{mb} = 100\text{ °C}$; see Figure 1	-	38	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$; see Figure 4	-	216	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; see Figure 2	-	42	W
T_{stg}	storage temperature		-55	175	°C
T_j	junction temperature		-55	175	°C
$T_{sld(M)}$	peak soldering temperature		-	260	°C
V_{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	190	-	V
Source-drain diode					
I_S	source current	$T_{mb} = 25\text{ °C}$	-	38	A
I_{SM}	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$	-	216	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ °C}$; $I_D = 54\text{ A}$; $V_{sup} \leq 30\text{ V}$; $R_{GS} = 50\text{ }\Omega$; unclamped; see Figure 3	-	12	mJ

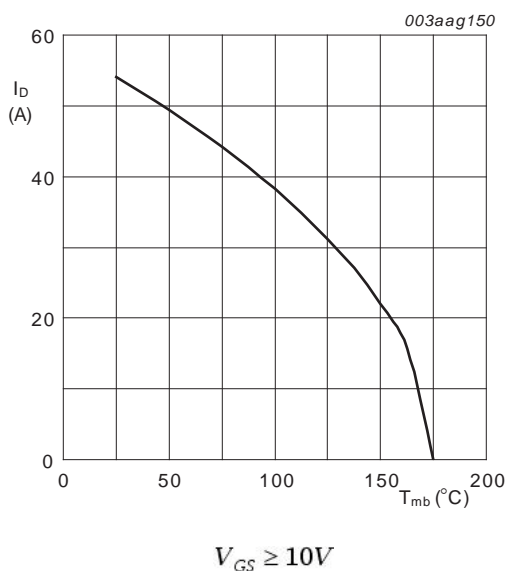


Fig 1. Continuous drain current as a function of mounting base temperature

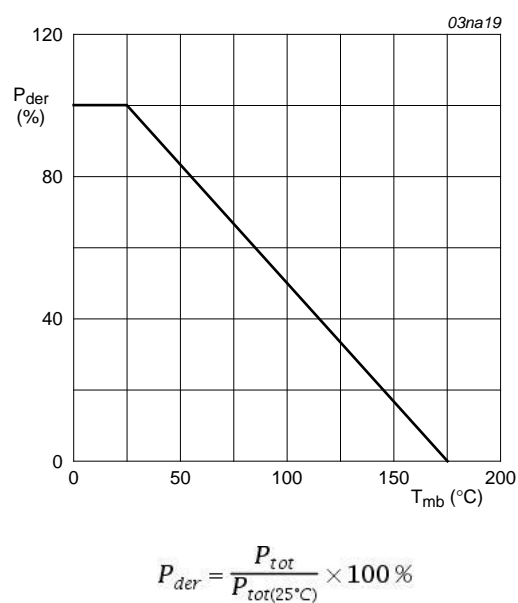


Fig 2. Normalized total power dissipation as a function of mounting base temperature

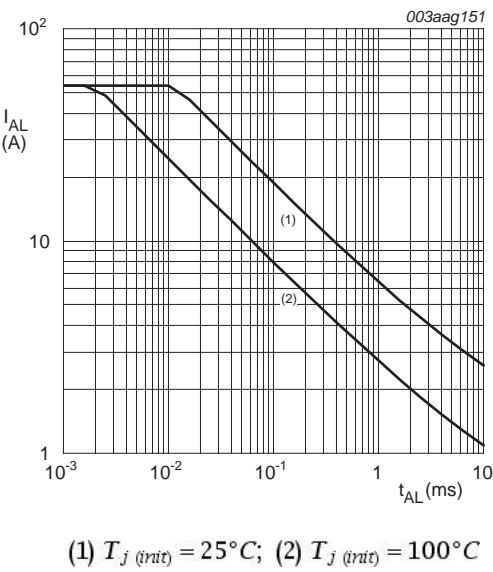


Fig 3. Single pulse avalanche rating; avalanche current as a function of avalanche time

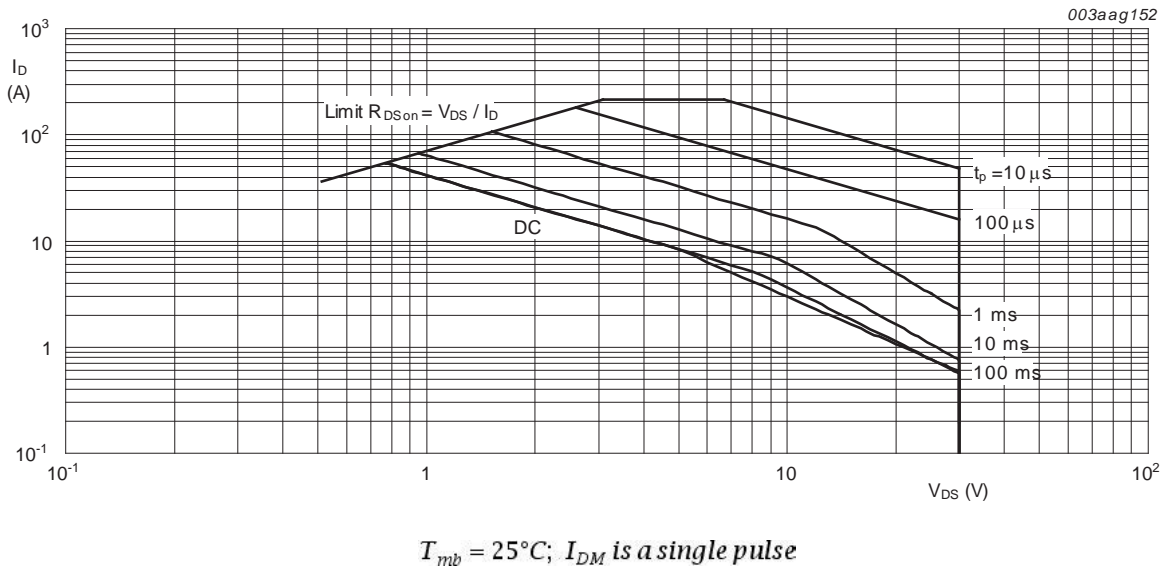
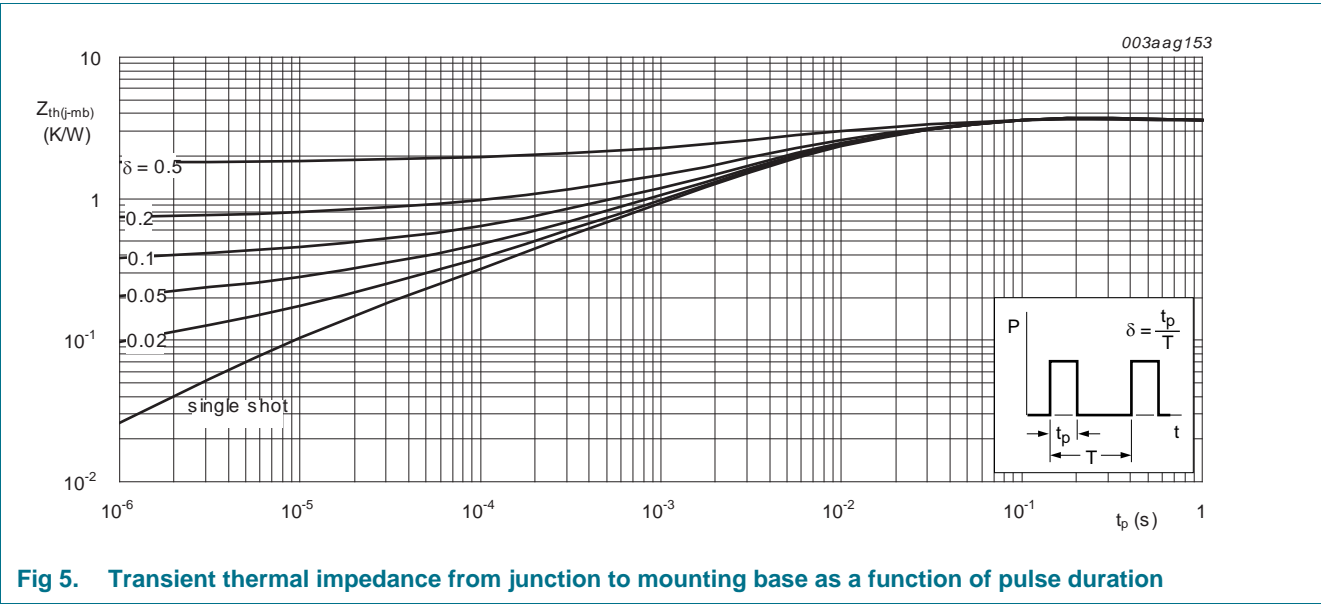


Fig 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	3.38	3.61	K/W



6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250\ \mu A$; $V_{GS} = 0\ V$; $T_j = 25\ ^\circ C$	30	-	-	V
		$I_D = 250\ \mu A$; $V_{GS} = 0\ V$; $T_j = -55\ ^\circ C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1\ mA$; $V_{DS} = V_{GS}$; $T_j = 25\ ^\circ C$; see Figure 10	1.05	1.59	1.95	V
		$I_D = 10\ mA$; $V_{DS} = V_{GS}$; $T_j = 150\ ^\circ C$; see Figure 11	0.5	-	-	V
		$I_D = 1\ mA$; $V_{DS} = V_{GS}$; $T_j = -55\ ^\circ C$; see Figure 11	-	-	2.25	V
I_{DSS}	drain leakage current	$V_{DS} = 30\ V$; $V_{GS} = 0\ V$; $T_j = 25\ ^\circ C$	-	-	1	μA
		$V_{DS} = 30\ V$; $V_{GS} = 0\ V$; $T_j = 150\ ^\circ C$	-	-	100	μA
I_{GSS}	gate leakage current	$V_{GS} = 16\ V$; $V_{DS} = 0\ V$; $T_j = 25\ ^\circ C$	-	-	100	nA
		$V_{GS} = -16\ V$; $V_{DS} = 0\ V$; $T_j = 25\ ^\circ C$	-	-	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\ V$; $I_D = 15\ A$; $T_j = 25\ ^\circ C$; see Figure 12	-	8.5	10	mΩ
		$V_{GS} = 4.5\ V$; $I_D = 15\ A$; $T_j = 150\ ^\circ C$; see Figure 12 ; see Figure 13	-	-	16.6	mΩ
		$V_{GS} = 10\ V$; $I_D = 15\ A$; $T_j = 25\ ^\circ C$; see Figure 12	-	6.7	7.9	mΩ
		$V_{GS} = 10\ V$; $I_D = 15\ A$; $T_j = 150\ ^\circ C$; see Figure 12 ; see Figure 13	-	-	13.2	mΩ
R_G	gate resistance	$f = 1\ MHz$	-	2.2	4.4	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 15\ A$; $V_{DS} = 15\ V$; $V_{GS} = 10\ V$; see Figure 14 ; see Figure 15	-	15	-	nC
		$I_D = 15\ A$; $V_{DS} = 15\ V$; $V_{GS} = 4.5\ V$; see Figure 14 ; see Figure 15	-	7	-	nC
		$I_D = 0\ A$; $V_{DS} = 0\ V$; $V_{GS} = 10\ V$	-	13	-	nC
Q_{GS}	gate-source charge	$I_D = 15\ A$; $V_{DS} = 15\ V$; $V_{GS} = 4.5\ V$; see Figure 14 ; see Figure 15	-	2.1	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	1.5	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	0.6	-	nC
Q_{GD}	gate-drain charge		-	2.3	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 15\ A$; $V_{DS} = 15\ V$; see Figure 14 ; see Figure 15	-	2.6	-	V
C_{iss}	input capacitance	$V_{DS} = 15\ V$; $V_{GS} = 0\ V$; $f = 1\ MHz$; $T_j = 25\ ^\circ C$; see Figure 16	-	848	-	pF
C_{oss}	output capacitance		-	207	-	pF
C_{rss}	reverse transfer capacitance		-	70	-	pF

Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t _{d(on)}	turn-on delay time	V _{DS} = 15 V; R _L = 1 Ω; V _{GS} = 4.5 V; R _{G(ext)} = 4.7 Ω	-	15	-	ns
t _r	rise time		-	11	-	ns
t _{d(off)}	turn-off delay time		-	19	-	ns
t _f	fall time		-	7	-	ns
Q _{oss}	output charge	V _{GS} = 0 V; V _{DS} = 15 V; f = 1 MHz; T _j = 25 °C	-	5	-	nC

Source-drain diode

V _{SD}	source-drain voltage	I _S = 15 A; V _{GS} = 0 V; T _j = 25 °C; see Figure 17	-	0.85	1.1	V
t _{rr}	reverse recovery time	I _S = 15 A; dI _S /dt = -100 A/μs; V _{GS} = 0 V; V _{DS} = 15 V	-	21	-	ns
Q _r	recovered charge		-	13	-	nC
t _a	reverse recovery rise time	V _{GS} = 0 V; I _S = 15 A; dI _S /dt = -100 A/μs; V _{DS} = 15 V; see Figure 18	-	12	-	ns
t _b	reverse recovery fall time		-	9	-	ns

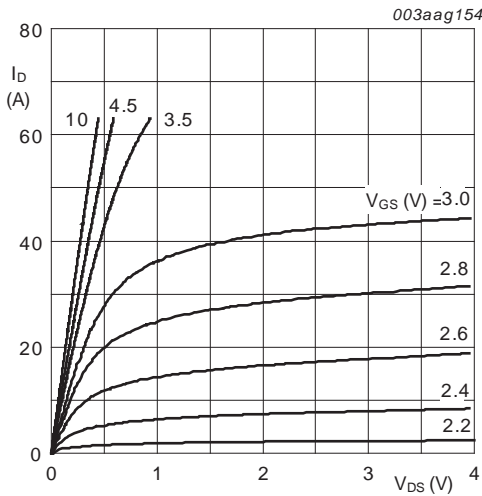


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values

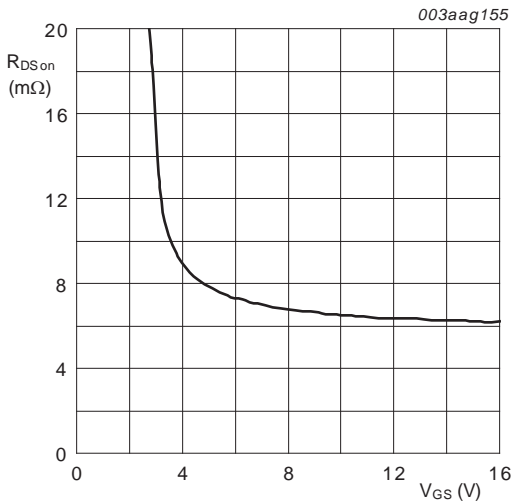
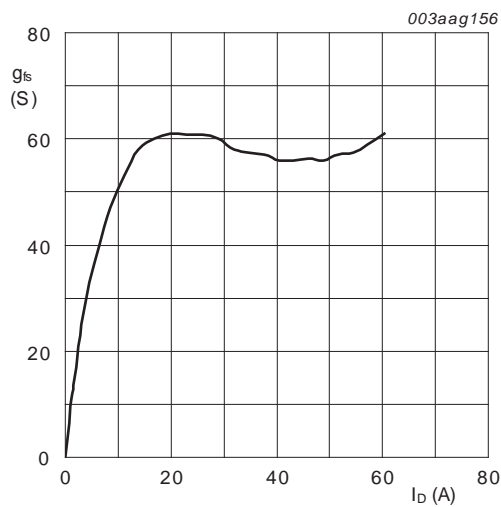
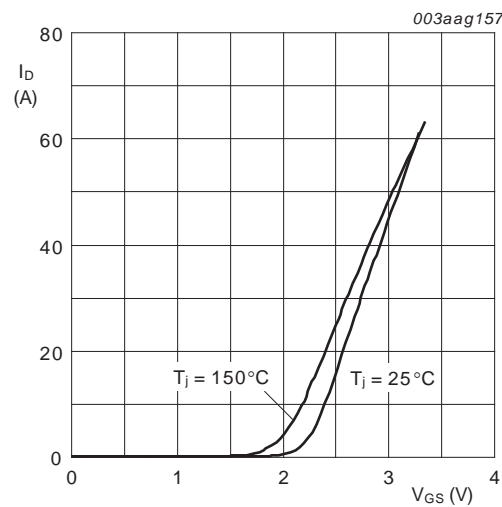


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values



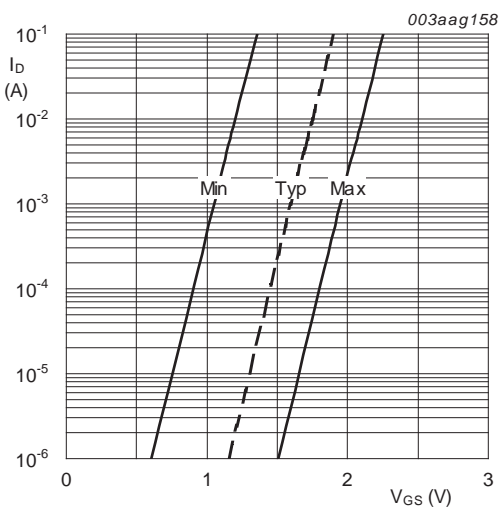
$T_j = 25^\circ\text{C}; V_{DS} = 10\text{V}$

Fig 8. Forward transconductance as a function of drain current; typical values



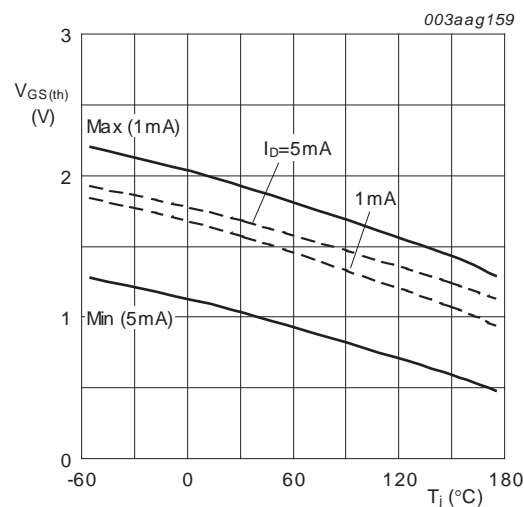
$V_{DS} = 10\text{V}$

Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values



$T_j = 25^\circ\text{C}; V_{DS} = 5\text{V}$

Fig 10. Sub-threshold drain current as a function of gate-source voltage



$V_{DS} = V_{GS}$

Fig 11. Gate-source threshold voltage as a function of junction temperature

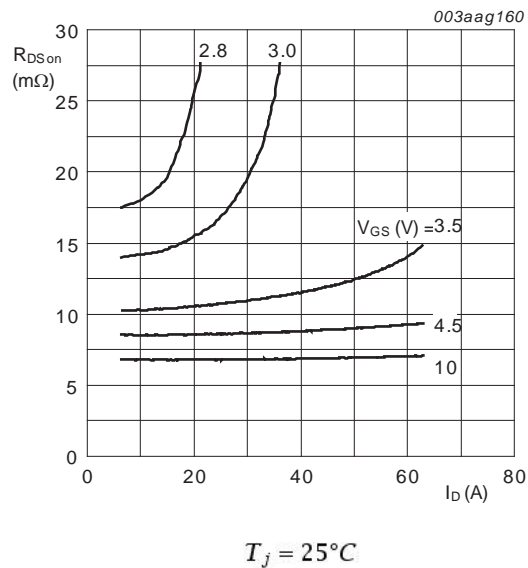


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

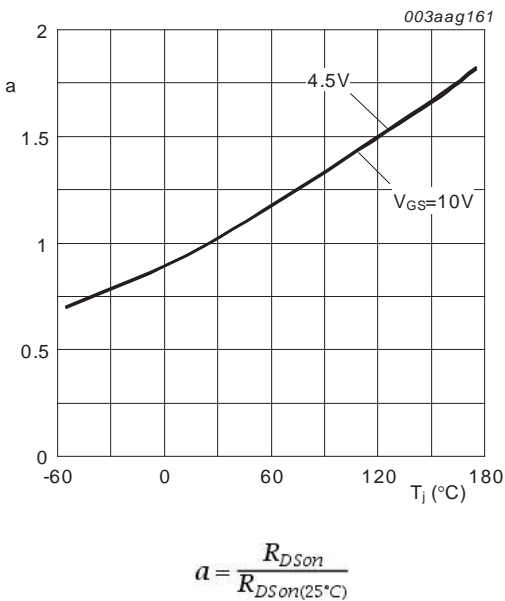


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

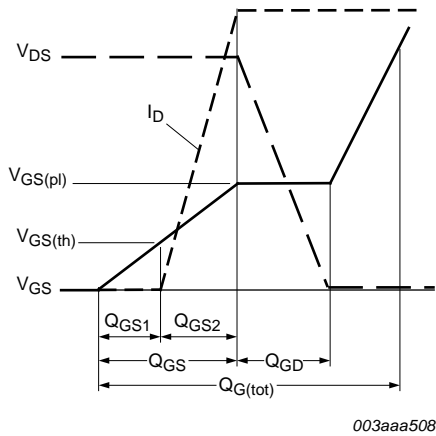


Fig 14. Gate charge waveform definitions

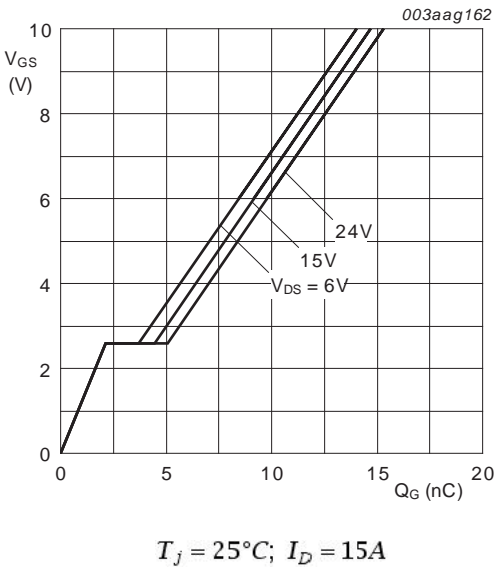


Fig 15. Gate-source voltage as a function of gate charge; typical values

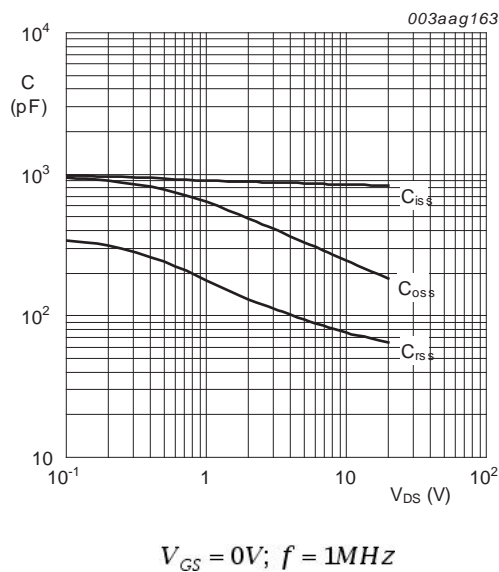


Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

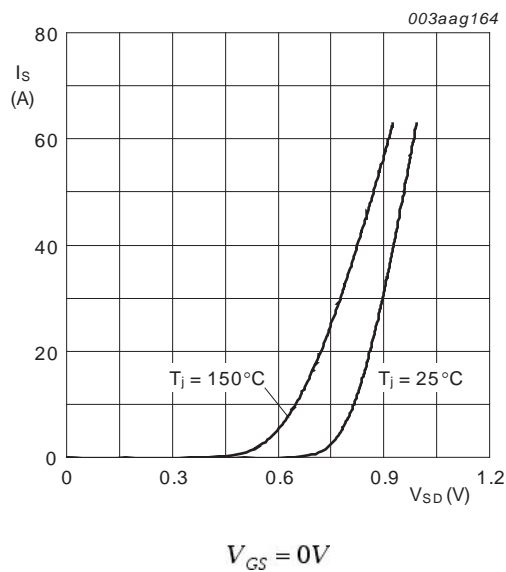


Fig 17. Source current as a function of source-drain voltage; typical values

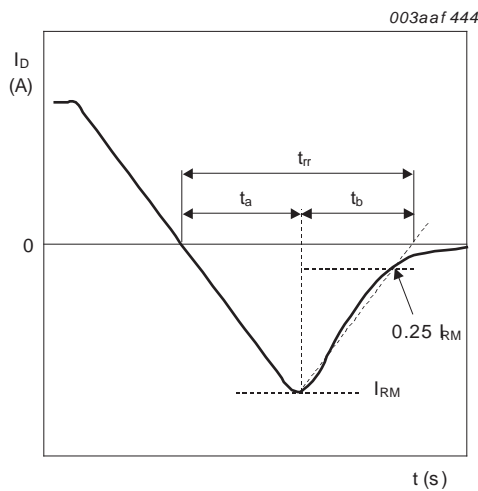
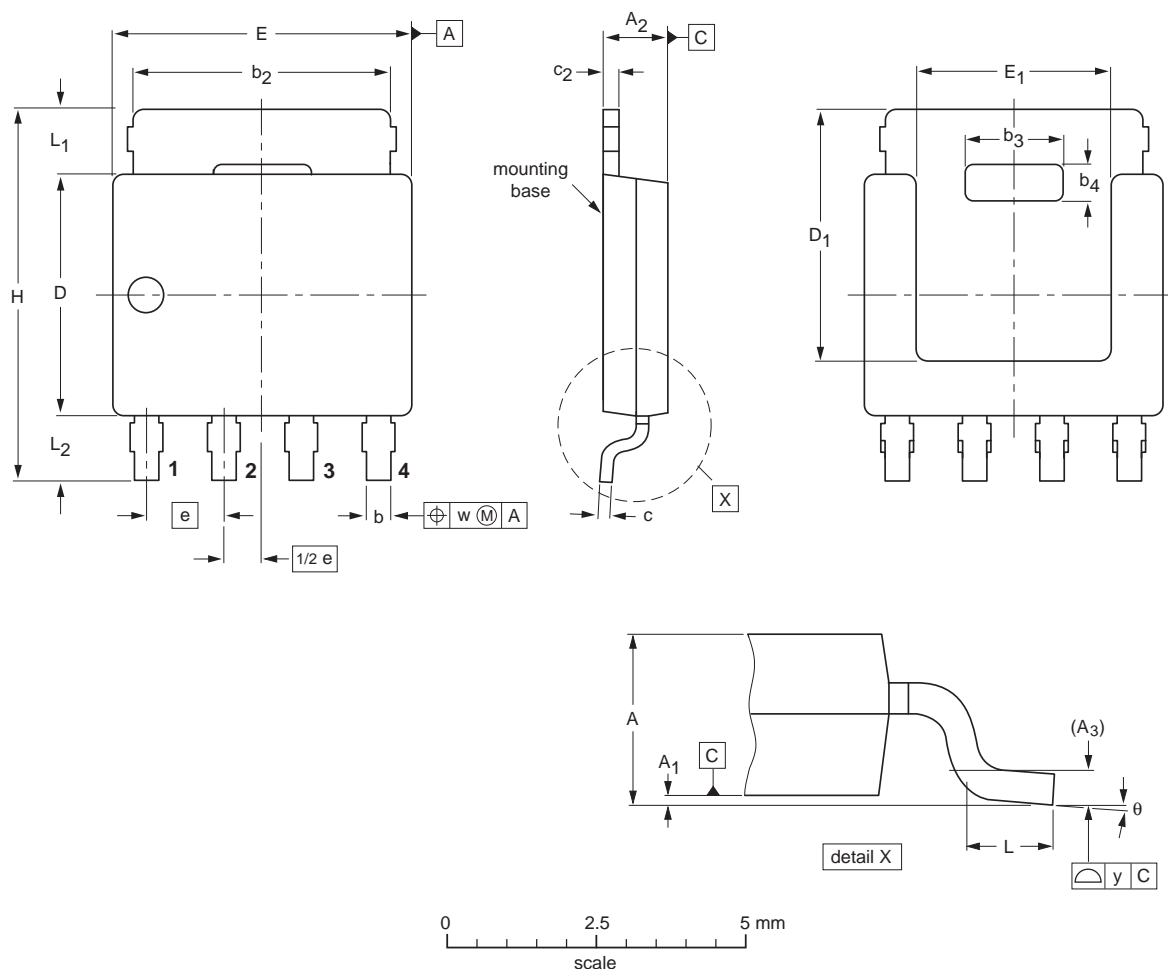


Fig 18. Reverse recovery timing definition

7. Package outline

Plastic single-ended surface-mounted package (LFPAK; Power-SO8); 4 leads

SOT669



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	A ₂	A ₃	b	b ₂	b ₃	b ₄	c	c ₂	D ⁽¹⁾	D _{max} ⁽¹⁾	E ⁽¹⁾	E ₁ ⁽¹⁾	e	H	L	L ₁	L ₂	w	y	θ
mm	1.20 1.01	0.15 0.00	1.10 0.95	0.25	0.50 0.35	4.41 3.62	2.2 2.0	0.9 0.7	0.25 0.19	0.30 0.24	4.10 3.80	4.20	5.0 4.8	3.3 3.1	1.27	6.2 5.8	0.85 0.40	1.3 0.8	1.3 0.8	0.25	0.1	8° 0°

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.


OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT669		MO-235				<div>06-03-16</div> <div>11-03-25</div>

Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN8R0-30YLC v.2	20110901	Product data sheet	-	PSMN8R0-30YLC v.1
Modifications:	• Data sheet status changed from objective to product.			
PSMN8R0-30YLC v.1	20110712	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status ^{[1] [2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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11. Contents

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